

(12) **United States Patent**  
**Wang et al.**

(10) **Patent No.:** **US 12,394,669 B2**  
(45) **Date of Patent:** **Aug. 19, 2025**

(54) **WET CLEANING WITH TUNABLE METAL RECESS FOR VIA PLUGS**

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(\*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 193 days.

(21) Appl. No.: **18/153,832**

(22) Filed: **Jan. 12, 2023**

(65) **Prior Publication Data**

US 2023/0163027 A1 May 25, 2023

**Related U.S. Application Data**

(60) Continuation of application No. 17/120,668, filed on Dec. 14, 2020, now Pat. No. 11,557,512, which is a (Continued)

(51) **Int. Cl.**

**H01L 21/768** (2006.01)

**H01L 23/00** (2006.01)

**H01L 23/522** (2006.01)

(52) **U.S. Cl.**

CPC .. **H01L 21/76831** (2013.01); **H01L 21/76805** (2013.01); **H01L 21/76877** (2013.01); **H01L 23/5226** (2013.01); **H01L 23/564** (2013.01)

(58) **Field of Classification Search**

CPC ..... H01L 21/76831; H01L 21/76805; H01L 21/76877; H01L 23/5226; H01L 23/564  
See application file for complete search history.

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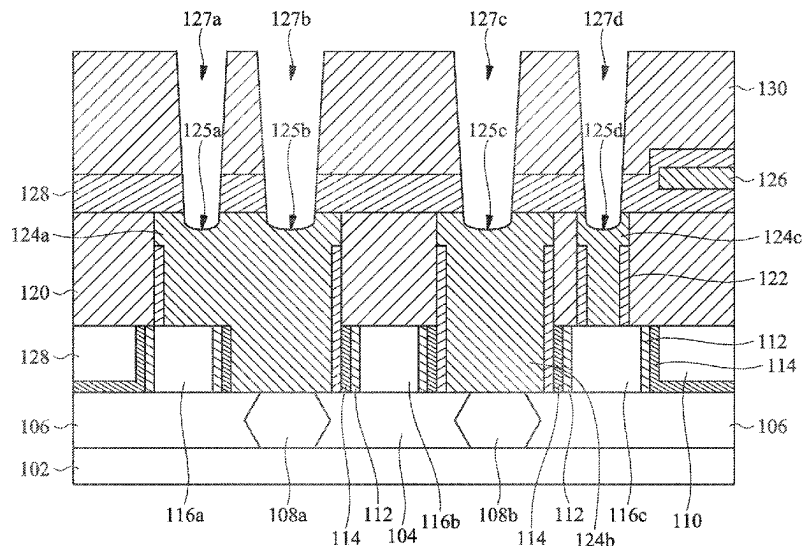
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(57) **ABSTRACT**

In one exemplary aspect, a method comprises providing a semiconductor structure having a substrate, one or more first dielectric layers over the substrate, a first metal plug in the one or more first dielectric layers, and one or more second dielectric layers over the one or more first dielectric layers and the first metal plug. The method further comprises etching a via hole into the one or more second dielectric layers to expose the first metal plug, etching a top surface of the first metal plug to create a recess thereon, and applying a metal corrosion protectant comprising a metal corrosion inhibitor to the top surface of the first metal plug.

**20 Claims, 5 Drawing Sheets**

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**Related U.S. Application Data**

division of application No. 15/939,025, filed on Mar.  
28, 2018, now Pat. No. 10,867,844.

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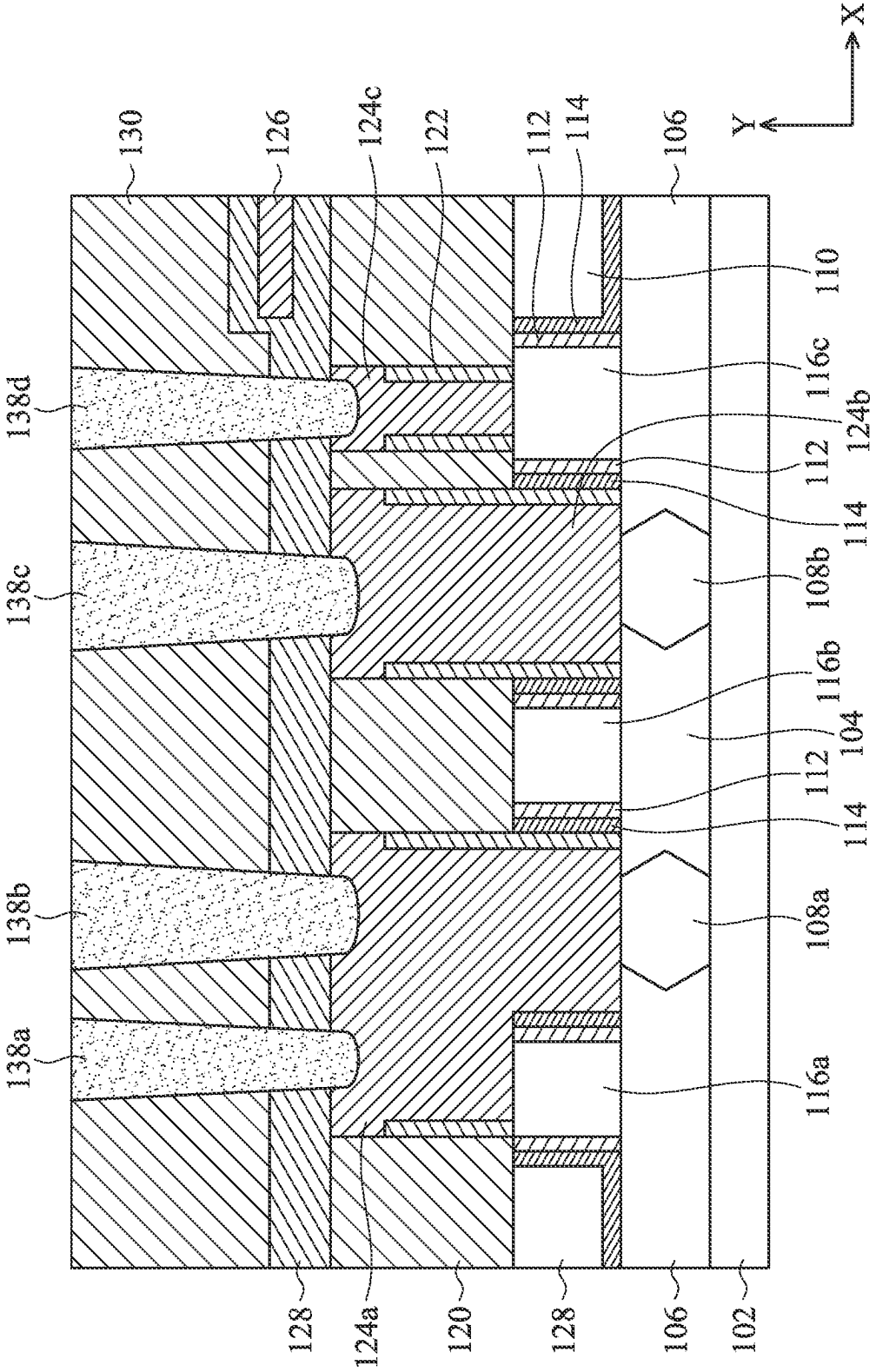


FIG. 1

200

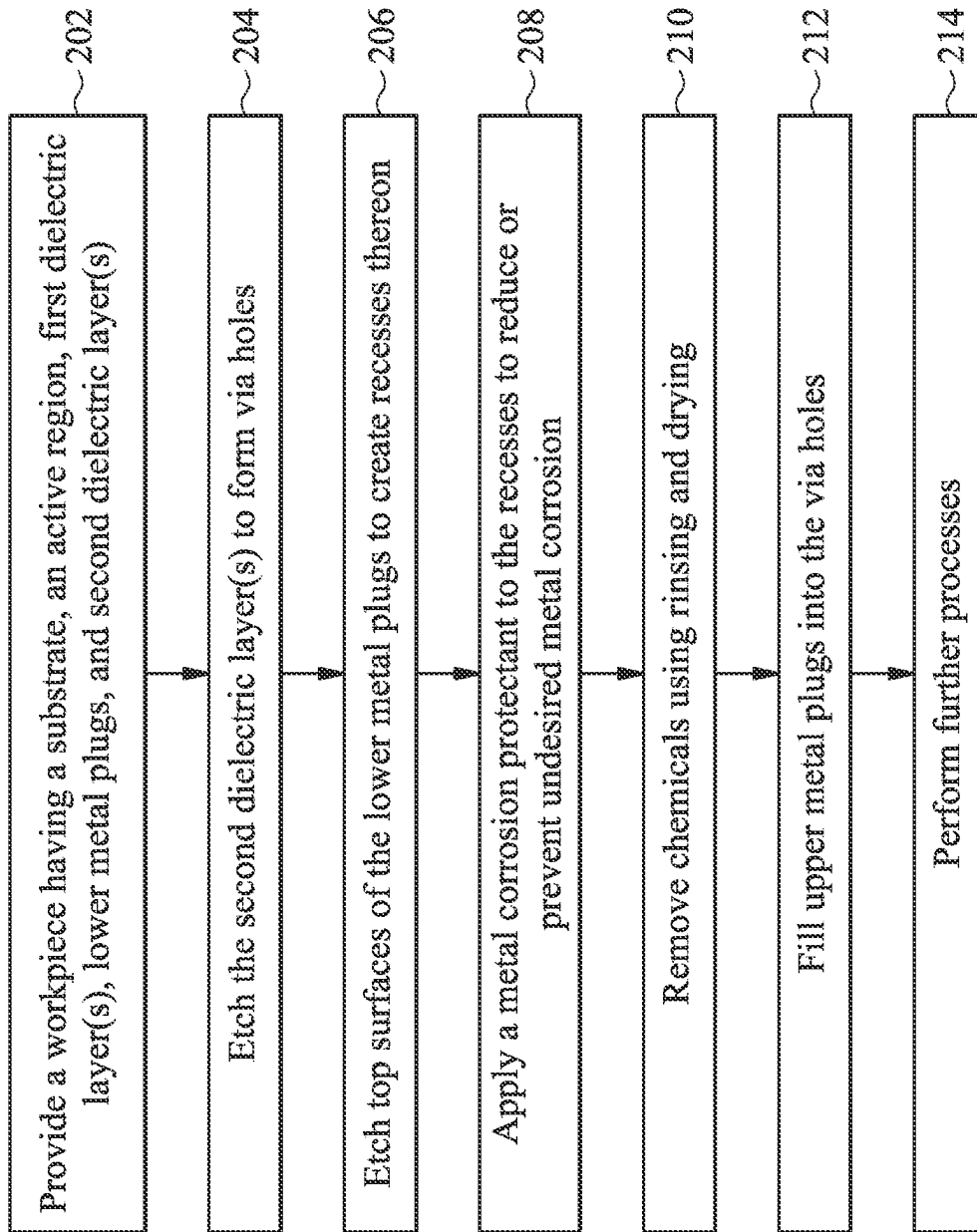


FIG. 2

100

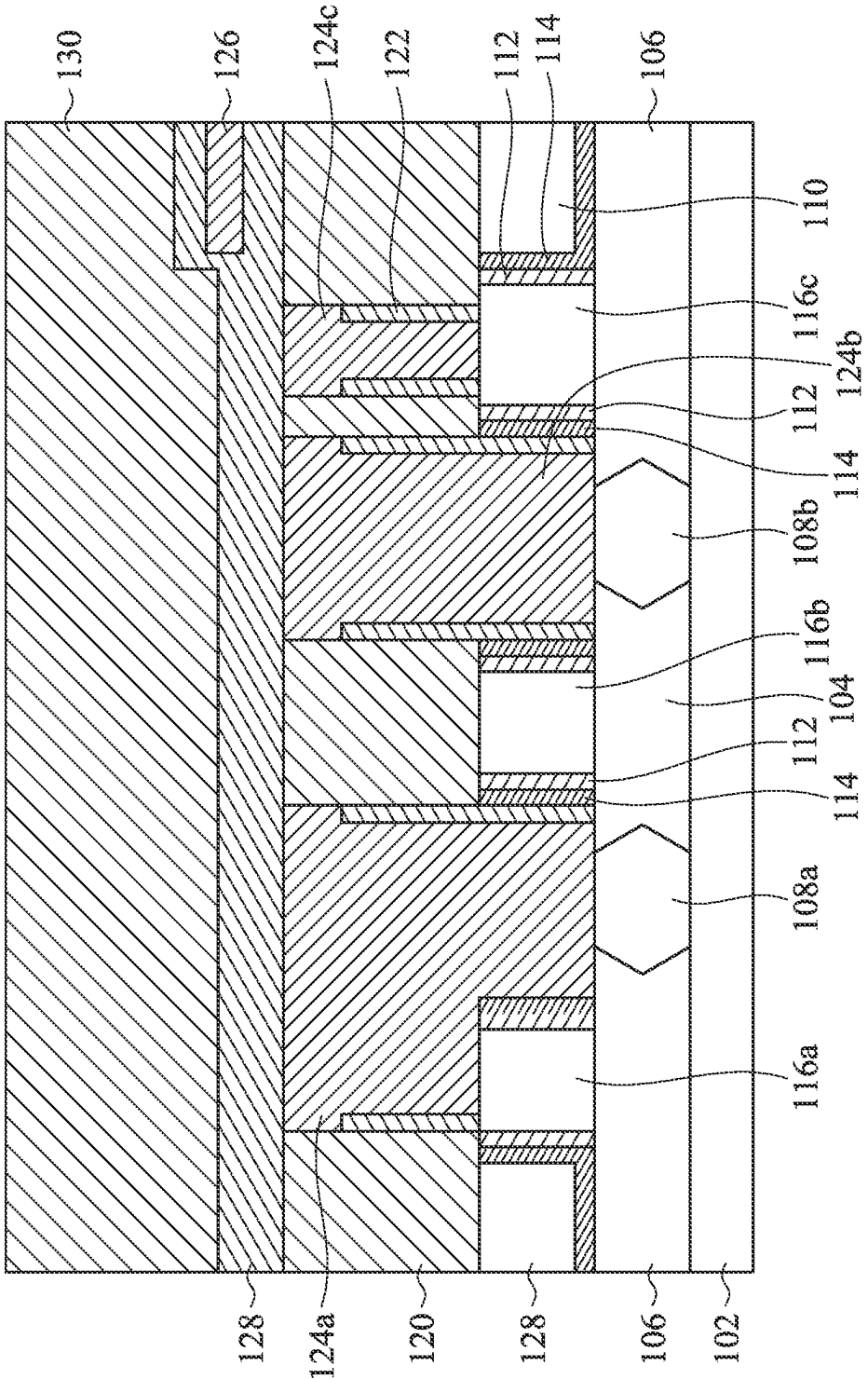


FIG. 3

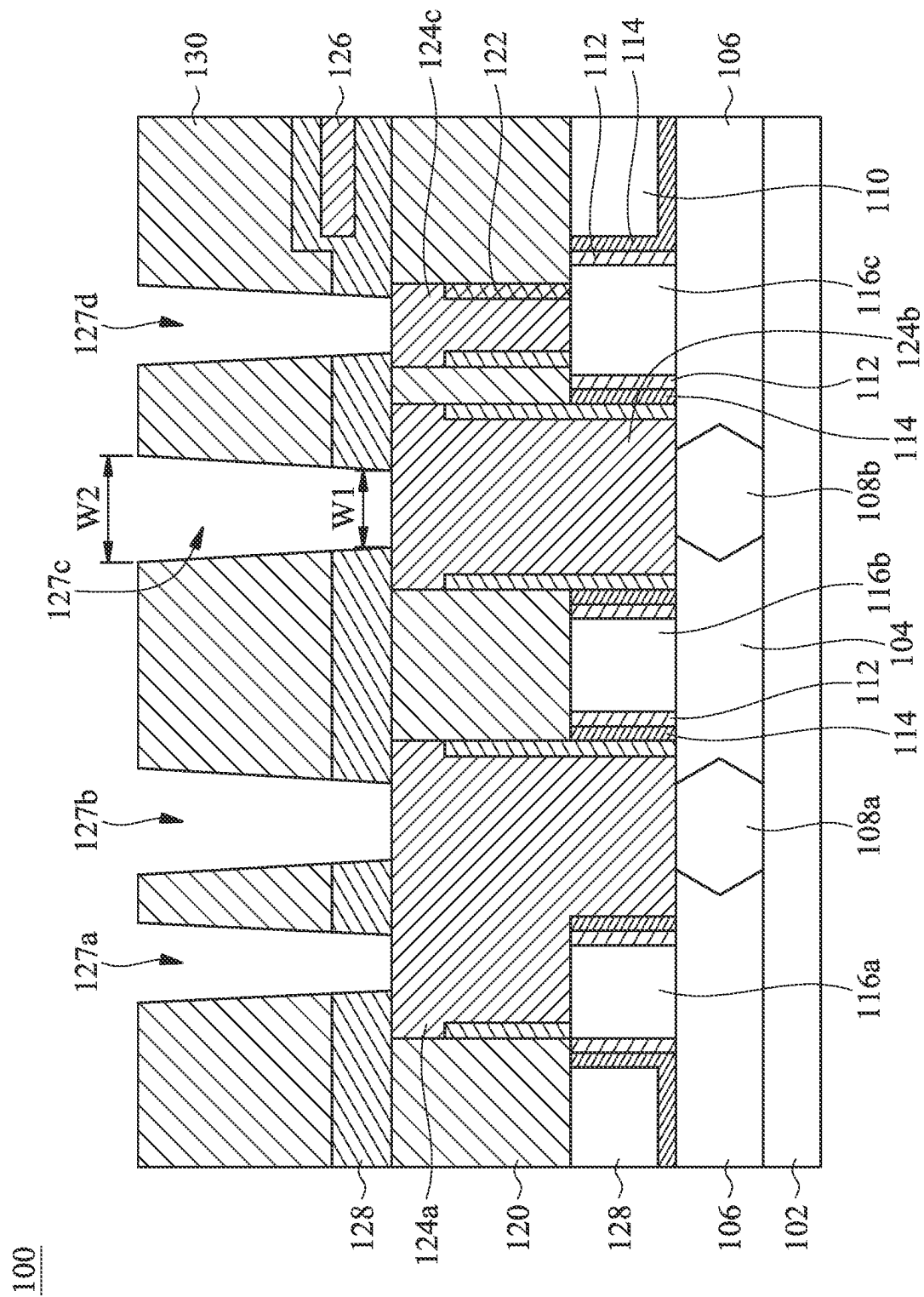


FIG. 4

100

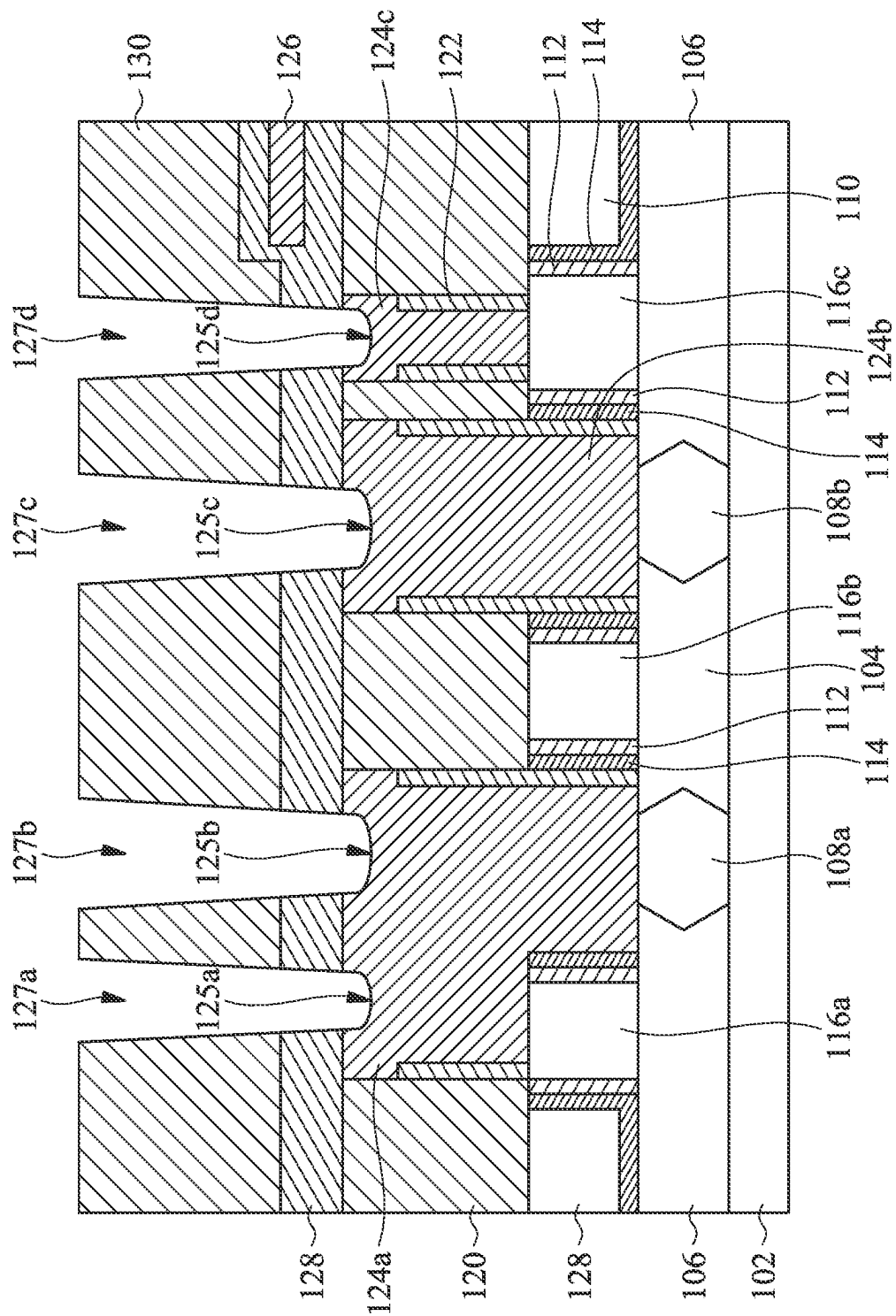


FIG. 5

## WET CLEANING WITH TUNABLE METAL RECESS FOR VIA PLUGS

This is a continuation application of U.S. patent application Ser. No. 17/120,668, filed Dec. 14, 2020, which is a divisional application of U.S. patent application Ser. No. 15/939,025, filed Mar. 28, 2018, now U.S. Pat. No. 10,867,844, the entire disclosures of which are incorporated herein by reference.

### BACKGROUND

The semiconductor integrated circuit (IC) industry has experienced rapid growth. Technological advances in IC materials and design have produced generations of ICs where each generation has smaller and more complex circuits than the previous generation. In the course of IC evolution, functional density (i.e., the number of interconnected devices per chip area) has generally increased while geometry size (i.e., the smallest component (or line) that can be created using a fabrication process) has decreased. This scaling down process generally provides benefits by increasing production efficiency and lowering associated costs. But these advances have also increased the complexity of processing and manufacturing ICs. For example, via plugs are used across multiple dielectric layers as metal interconnect. As the down-scaling continues, via plugs become smaller and smaller. As interface area between upper and lower via plugs decreases, contact resistance increases, sometimes rendering devices unusable. Improvements in these areas are desired.

### BRIEF DESCRIPTION OF THE DRAWINGS

The present disclosure is best understood from the following detailed description when read with the accompanying figures. It is emphasized that, in accordance with the standard practice in the industry, various features are not drawn to scale and are used for illustration purposes only. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

FIG. 1 is a schematic diagram showing a cross-sectional view of a semiconductor structure constructed according to various embodiments of the present disclosure.

FIG. 2 is a flow chart showing a method for forming the semiconductor structure shown in FIG. 1, according to various embodiments of the present disclosure.

FIGS. 3, 4, and 5 illustrate cross-sectional views of a semiconductor structure during various fabrication stages various embodiments of the present disclosure.

### DETAILED DESCRIPTION

The following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is

for the sake of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed. Moreover, various features may be arbitrarily drawn in different scales for the sake of simplicity and clarity.

Further, spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature’s relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as being “below” or “beneath” other elements or features would then be oriented “above” the other elements or features. Thus, the exemplary term “below” can encompass both an orientation of above and below. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

The present disclosure is generally related to semiconductor devices and fabrication methods, and more particularly to metal plugs for interconnecting conductive features between different layers of an integrated circuit (IC). In order to minimize contact resistance between metal vias across multiple layers, forming metal recesses on a lower via provides an approach for reducing contact resistance by increasing contact area. But, once a metal recess is formed during a post-via wet cleaning process, it is difficult to prevent undesirable corrosion of the metal, which negatively impacts metal integrity and uncontrollably alters the profile of the recess. The wet cleaning process disclosed herein realizes in-situ metal recess and corrosion suppression, thereby creating determinative metal recesses without further metal corrosion. Metal recesses may thus have tunable and uniform profiles, which help improve device performance.

FIG. 1 is a schematic diagram illustrating a cross-sectional view of a semiconductor device (or semiconductor structure) 100, constructed according to embodiments of the present disclosure. The device 100 includes a substrate 102, an active region 104 disposed on the substrate 102, and isolation structures 106 that isolate the active region 104 from other active regions not shown in FIG. 1. Various active and passive devices may be built in or on active regions including 104, such as p-type field effect transistors (PFETs), n-type FETs (NFETs), multi-gate FETs such as FinFETs, metal-oxide semiconductor field effect transistors (MOSFETs), complementary metal-oxide semiconductor (CMOS) transistors, bipolar transistors, high voltage transistors, high frequency transistors, static random access memory (SRAM) cells, other memory cells, resistors, capacitors, and inductors.

The device 100 further includes transistor source/drain (S/D) features including 108a and 108b; transistor gate stacks (or gate structures or gate features) including 116a, 116b, and 116c; gate spacers including 112 and 114; dielectric layers including 110, 120, and 130; lower plugs including 124a, 124b, and 124c; upper plugs including 138a, 138b, 138c, and 138d; a via barrier layer 122; a metal contact etch stop layer (MCESL) 128, and a conductive feature 126. The device 100 may include various other features not shown in FIG. 1. The device 100’s components are further described below.

The substrate 102 is a semiconductor substrate (e.g., a silicon wafer) in the present embodiment. Alternatively, the



substrate **102** may comprise another elementary semiconductor, such as germanium; a compound semiconductor including silicon carbide, gallium nitride, gallium arsenide, gallium phosphide, indium phosphide, indium arsenide, and indium antimonide; an alloy semiconductor including silicon germanium, gallium arsenide phosphide, aluminum indium phosphide, aluminum gallium arsenide, gallium indium arsenide, gallium indium phosphide, and gallium indium arsenide phosphide; or combinations thereof. The substrate **102** may include indium tin oxide (ITO) glass, include silicon on insulator (SOI) substrate, be strained and/or stressed for performance enhancement, include epitaxial regions, doped regions, and/or include other suitable features and layers.

The active region **104** may include one or more layers of semiconductor materials such as silicon or silicon germanium, and may be doped with proper dopants for forming active or passive devices. In an embodiment, the active region **104** includes multiple alternating layers of semiconductor materials (e.g., with multiple layers of silicon and multiple layers of silicon germanium alternately stacked). The active region **104** may be a planar structure, for example, for forming planar transistors. Alternatively or additionally, the active region **104** may include three-dimensional (3D) structures such as fins, e.g., for forming multi-gate or 3D transistors such as FinFETs.

The active region **104** may be patterned by any suitable method. For example, the active region **104** may be patterned using photolithography techniques including double-patterning or multi-patterning processes. Double-patterning or multi-patterning processes combine photolithography and self-aligned processes, allowing patterns to be created with pitches smaller than what is otherwise obtainable using a single, direct photolithography process. In an embodiment of patterning the active region **104**, a sacrificial layer is first formed over the substrate **102** and patterned using a photolithography process. Spacers are formed alongside the patterned sacrificial layer using a self-aligned process. The sacrificial layer is then removed, and remaining spacers or mandrels may then be used as a masking element for patterning the active region **104**. For example, the masking element may be used for etching depressions into semiconductor layers over or in the substrate **102**, leaving the active region **104** on the substrate **102**. Etching the depressions using the masking element may use dry etching, wet etching, reactive ion etching (RIE), and/or other suitable processes.

The isolation structures **106** may include silicon oxide (SiO<sub>2</sub>), silicon nitride (Si<sub>3</sub>N<sub>4</sub>), silicon oxynitride (SiON), fluoride-doped silicate glass (FSG), a low-k dielectric material, and/or other suitable insulating material. In an embodiment, the isolation structures **106** are formed by etching trenches in or over the substrate **102** (e.g., as part of the process of forming the active region **104**), filling the trenches with an insulating material, and performing a chemical mechanical planarization (CMP) process and/or an etch back process to the insulating material, thereby leaving the remaining insulating material as the isolation structures **106**. Other types of isolation structures may also be suitable, such as field oxide and "LOCAl Oxidation of Silicon" (LOCOS). The isolation structures **106** may include a multi-layer structure, for example, having one or more liner layers (on surfaces of the substrate **102** and the active region **104**) and a main isolating layer over the one or more liner layers.

The S/D features **108a** and **108b** may include n-type doped silicon for NFETs, p-type doped silicon germanium for PFETs, or other suitable materials. The S/D features **108a** and **108b** may be formed by etching depressions in the

active region **104** adjacent to the gate spacers **112** and **114**, and then epitaxially growing semiconductor materials in the depressions. The epitaxially grown semiconductor materials may be doped with proper dopants in-situ or ex-situ. The S/D features **108a** and **108b** may have any suitable shape and may be wholly or partially embedded in the active region **104**.

The gate spacers **112** may include a dielectric material, such as silicon oxide or silicon oxynitride. The gate spacers **114** may include a dielectric material, such as silicon oxide, silicon nitride, silicon oxynitride, silicon carbide, other dielectric material, or combinations thereof. The gate spacers **112** and **114** may be formed by deposition (e.g., chemical vapor deposition (CVD) or physical vapor deposition (PVD)) and etching processes.

Each gate stack (e.g., **116a**, **116b**, or **116c**) may include a gate dielectric layer and a gate electrode layer, and may further include an interfacial layer under the gate dielectric layer. The interfacial layer may include a dielectric material such as SiO<sub>2</sub> or SiON, and may be formed by chemical oxidation, thermal oxidation, atomic layer deposition (ALD), CVD, and/or other suitable methods. The gate dielectric layer may include SiO<sub>2</sub> or a high-k dielectric material such as hafnium silicon oxide (HfSiO), hafnium oxide (HfO<sub>2</sub>), alumina (Al<sub>2</sub>O<sub>3</sub>), zirconium oxide (ZrO<sub>2</sub>), lanthanum oxide (La<sub>2</sub>O<sub>3</sub>), titanium oxide (TiO<sub>2</sub>), yttrium oxide (Y<sub>2</sub>O<sub>3</sub>), strontium titanate (SrTiO<sub>3</sub>), or a combination thereof. The gate dielectric layer may be deposited using CVD, PVD, ALD, and/or other suitable methods.

The gate electrode layer of the gate stack **116a**, **116b**, or **116c** may include polysilicon and/or one or more metal layers. For example, the gate electrode layer may include work function metal layer(s), conductive barrier layer(s), and metal fill layer(s). The work function metal layer may be a p-type or an n-type work function layer depending on device type. The p-type work function layer may comprise titanium aluminum nitride (TiAlN), titanium nitride (TiN), tantalum nitride (Ta<sub>2</sub>N), ruthenium (Ru), molybdenum (Mo), tungsten (W), platinum (Pt), another suitable metal, or combinations thereof. The n-type work function layer may comprise titanium (Ti), aluminum (Al), tantalum carbide (TaC), tantalum carbide nitride (TaCN), tantalum silicon nitride (TaSiN), titanium aluminum nitride (TiAlN), titanium silicon nitride (TiSiN), another suitable metal, or combinations thereof. The metal fill layer may include aluminum (Al), tungsten (W), cobalt (Co), and/or other suitable materials. The gate electrode layer may be deposited using methods such as CVD, PVD, plating, and/or other suitable processes.

The gate stacks **116a-116c** may be formed by any suitable processes such as gate-first processes and gate-last processes. In an example gate-first process, various material layers are deposited and patterned to become the gate stacks **116a-116c** before the S/D features **108a** and **108b** are formed. In an example gate-last process (also called a gate replacement process), temporary gate structures are formed first. Then, after transistor source/drain features **108** are formed, the temporary gate structures are removed and replaced with the gate stacks **116a-116c**. In the embodiment shown in FIG. 1, the gate stack **116b** is disposed over a channel region of a transistor and functions as a gate terminal. Although not shown in this cross-sectional view, a metal plug may be disposed over the gate stack **116b** (e.g., e.g., to apply an adjustable voltage to the gate stack **116b** in order to control the channel region between the S/D features **108a** and **108b**).

The dielectric layers **110**, **120**, and **130** are also called interlayer dielectric (ILD) layers. Each of the ILD layers **110**, **120**, and **130** may comprise tetraethylorthosilicate (TEOS) oxide, un-doped silicate glass, or doped silicon oxide such as borophosphosilicate glass (BPSG), fused silica glass (FSG), phosphosilicate glass (PSG), boron doped silicon glass (BSG), and/or other suitable dielectric materials. Each ILD layer may be formed by plasma enhanced CVD (PECVD), flowable CVD (FCVD), or other suitable methods. The ILD layers **110**, **120**, and **130** may have the same or different materials.

As shown in FIG. 1, the barrier layer **122** includes barrier features disposed on sidewalls of the lower plugs **124a-124c**. In some embodiments, a barrier feature includes dual barriers—a first barrier on sidewalls of the lower plugs **124a-124c** and a second barrier over sidewalls of the first barrier (e.g., between the first barrier and the ILD layer **120**). In an embodiment, the first barrier includes TiN or TaN, and the second barrier includes silicon nitride (Si<sub>3</sub>N<sub>4</sub>). The barrier layer **122** may be formed by CVD, ALD, or other suitable methods.

The lower plugs **124a** and **124b** are disposed over and are in electrical contact with the S/D features **108a** and **108b**, respectively. In the embodiment shown in FIG. 1, the plug **124a** for example is directly connected to the S/D feature **108** without an intermediate silicide feature. In an alternative embodiment, the plug **124a** is coupled to the S/D feature **108** through a silicide feature. The silicide feature may be formed by a process that includes depositing a metal layer, annealing the metal layer such that the metal layer reacts with the semiconductor material(s) in the S/D feature **108a** to form silicide, and then removing the non-reacted metal layer. The silicide feature may include nickel silicide, titanium silicide, cobalt silicide, or other suitable silicidation or germanosilicidation. The lower plug **124c** is disposed over and is in electrical contact (directly or indirectly) with the gate stack **116c**. The lower plugs **124a-124c** may be formed by CVD, PVD, plating, or other suitable methods. The lower plugs **124a-124c** may include tungsten (W), cobalt (Co), copper (Cu), and/or other suitable materials. Note that metal plugs disclosed herein, such as the lower plugs **124a-124c** and the upper plugs **138a-138d**, may also contain non-metal material(s). A metal plug is sometimes also called a via, a via plug, a metal contact, or a contact plug.

The MCESL **128** may comprise silicon nitride, silicon oxynitride, silicon nitride with oxygen (O) or carbon (C) elements, and/or other materials; and may be formed by CVD, PVD, ALD, or other suitable methods. The MCESL **128** may include multiple layers (e.g., multiple dielectric layers deposited at different times).

The conductive feature **126** may include any suitable conductive material(s). In an embodiment, the conductive feature **126** provides relatively high electrical resistance (e.g., as part of a resistor). To further this embodiment, the conductive feature **126** may include titanium nitride or other suitable material(s). As shown in FIG. 1, the MCESL **128** has multiple layers, and the conductive feature **126** may be formed by a procedure that includes depositing a conductive layer (e.g., TiN) over a first layer of the MCESL **128**, forming a dielectric hard mask layer over the conductive layer, patterning the dielectric hard mask layer and the conductive layer, and depositing a second layer of the MCESL **128**, thereby embedding the conductive feature **126** within the MCESL **128**.

The upper plugs **138a-138d** are disposed over and are in electrical contact with the lower plugs **124a-124c**, as shown in FIG. 1. Note that bottom portions of the upper plugs

**138a-138d** extend into recessed top portions of the lower plugs **124a-124c**. Such a curved interface between the upper and lower plugs minimizes contact resistance. The formation of this interface is further described below.

FIG. 2 is a flow chart illustrating a method **200** for forming the semiconductor device **100** in accordance with some embodiments. The method **200** is merely an example, and is not intended to limit the present disclosure beyond what is explicitly recited in the claims. Additional operations can be executed before, during, and after the method **200**, and some operations described can be replaced, eliminated, or moved around for additional embodiments of the method **200**. The method **200** is described below in conjunction with FIGS. 3-5, which illustrate cross-sectional views of the semiconductor device **100** during various fabrication stages.

At operation **202**, the method **200** provides, or is provided with, a starting device structure (workpiece) **100**, such as shown in FIG. 3. The device structure **100** includes the substrate **102**, the active region **104**, the isolation structures **106**, the S/D features **108a** and **108b**, the gate stacks **116a-116c**, the gate spacers **112** and **114**, the ILD layers **110**, **120**, and **130**, the lower plugs **124a-124c**, the barrier layer **122**, the conductive feature **126**, and the MCESL **128**. These various features have been discussed above with reference to FIG. 1.

Referring to FIG. 4, at operation **204**, the method **200** etches the ILD layer **130** and the MCESL **128** to form via holes including **127a**, **127b**, **127c**, and **127d**. The via holes **127a-127d** are etched above their respective lower plugs **124a-124c**. Specifically, as an example, two via holes **127a** and **127b** are etched over the lower plug **124a**, which is relatively wider than the rest of the lower plugs **124b** and **124c**. The via hole **127c** is etched over the lower plug **124b**, and the via hole **127d** is etched over the lower plug **124c**. Thus, a lower plug may have one or more via holes etched thereon. In some embodiments, certain lower plugs may not have any via holes etched thereon. As shown in FIG. 4, the via holes **127a-127d** at least partially expose respective top surfaces of the lower plugs **124a-124c**.

In an embodiment, operation **204** includes a photolithography process and one or more etching processes. For example, operation **204** may form a patterned photoresist over the device **100** by photoresist coating, exposing, post-exposure baking, and developing. Then, the operation **204** etches the layers **128** and **130** using the patterned photoresist or a derivative as an etch mask to form the via holes **127**. The etching process may include wet etching, dry etching, reactive ion etching, or other suitable etching methods. For example, a dry etching process may implement an oxygen-containing gas, a fluorine-containing gas (e.g., CF<sub>4</sub>, SF<sub>6</sub>, CH<sub>2</sub>F<sub>2</sub>, CHF<sub>3</sub>, and/or C<sub>2</sub>F<sub>6</sub>), a chlorine-containing gas (e.g., Cl<sub>2</sub>, CHCl<sub>3</sub>, CCl<sub>4</sub>, and/or BCl<sub>3</sub>), a bromine-containing gas (e.g., HBr and/or CHBr<sub>3</sub>), an iodine-containing gas, or other suitable gases and/or plasmas, or combinations thereof. For example, a wet etching process may comprise etching in diluted hydrofluoric acid (DHF), potassium hydroxide (KOH) solution, ammonia, an acid solution (e.g., containing hydrofluoric acid (HF), nitric acid (HNO<sub>3</sub>), and/or acetic acid (CH<sub>3</sub>COOH)), or other suitable wet etchants, or combinations thereof. Following the etching process, the patterned photoresist is removed, for example, by resist stripping.

Following operation **204**, the method **200** enters into a wet cleaning process (sometimes called a post-via wet clean). The wet cleaning process disclosed herein includes multiple steps and serves multiple purposes (e.g., it creates recesses—on the top surfaces of the lower plugs **124a-**

124c—with tunable profiles and smooth surfaces). In the embodiment shown in FIG. 2, the wet cleaning process includes operations 206, 208, and 210, which are discussed below.

At operation 206, the method 200 etches the top portions of the lower plugs 124a-124c to deepen the via holes 138a-138d. Referring to FIG. 5, recesses including 125a, 125b, 125c, and 125d are created on top surfaces of the lower plugs 124a-124c. Operation 206 may be considered an extension of the etching process performed in operation 204, but may use different processes and materials from operation 204. For example, in some embodiments, operation 206 does not use a dry etching process but rather uses a wet etching process targeting lower plugs 124a-124c. As part of the wet cleaning process, operation 206 also removes any residues formed during operation 204 on the top surfaces of the lower plugs 124a-124c. Operation 206 may soak the device 100 (shown in FIG. 4) in a wet etchant containing diluted ammonium hydroxide (NH<sub>4</sub>OH), carbon dioxide (CO<sub>2</sub>) blended deionized (DI) water, ozone (O<sub>3</sub>) blended DI water, hydrogen peroxide (H<sub>2</sub>O<sub>2</sub>) blended DI water, or other suitable chemicals, or combinations thereof. The chemicals may have any suitable concentrations. In an embodiment, operation 206 uses hydrogen peroxide blended DI water with a H<sub>2</sub>O<sub>2</sub>:H<sub>2</sub>O volume ratio range between 1:5 and 1:30.

In an embodiment, operation 206 uses isotropic etching to create the recesses 125a-125d with smooth surface profiles. When isotropic etching is used, the depth and top opening area of the recesses 125a-125d are correlated, which leads to a bowl shaped cross-sectional profile. Dimensions of the recesses 125a-125d may be tunable or quantitatively controllable via adjustment of various process conditions such as etching time and temperature. For example, a prolonged immersion period in a wet etchant, or a higher temperature, or a combination of both leads to wider and deeper recesses 125a-125d. Different etching solutions and materials of the lower plugs 124a-124c may use different durations and temperatures. In some embodiments, the etching process in operation 206 lasts between 20 to 100 seconds (e.g., about 30 or about 50 seconds) and is performed between room temperature and about 67 degrees Celsius.

The tunable profiles of the recesses 125a-125d with smooth surfaces helps control contact resistance between the lower plugs 124a-124c and upper plugs 138a-138d (to be formed in operation 212). A wider and deeper recess leads to a larger interface area between a lower plug and an upper plug, thereby leading to a smaller contact resistance, but an overly wide and deep recess may have drawbacks such as damaging sidewalls of lower plugs (e.g., the lower plug 124c shown in FIG. 5) that are relatively narrower and causing metal contact leak. Since a lower plug may have one or more via holes etched thereon, the profiles of recesses on each lower plug may or may not be the same. In an embodiment, dimensions of the recesses 125a-125d are substantially equal or uniform.

Following operation 206, the wet etchant used in forming the recesses 125a-125d should be removed, e.g., using a drying process. One problem that has plagued some wet cleaning processes is that, even if ideal recesses were formed initially, during the drying process the wet etchant would continue to remove material(s) from top surfaces of the lower plugs 124a-124c, thereby leading to uneven and uncontrollable recess profiles. Such poor recess profiles reduces uniformity across lower plugs (e.g., different contact resistance values on different lower plugs), which reduces product yield. To solve this problem, at operation 208 the method 200 applies a metal corrosion protectant (sometimes

called a metal compatible chemical) to the recesses 125a-125d in order to reduce—or even prevent—undesired corrosion of the lower plugs 124a-124c. The metal corrosion protectant may be or include a metal corrosion inhibitor that decreases the corrosion rate of materials in the lower plugs 124a-124c. Different metals work with different corrosion inhibitors. Therefore, depending on the material makeup of the lower plugs 124a-124c, suitable corrosion inhibitors including commercially available inhibitors may be used.

The metal corrosion protectant is applied in a suitable manner. For example, the metal corrosion protectant may be applied right after (e.g., within 1, 2, 5, or 10 seconds) the recesses 125a-125d have reached pre-defined target profiles in order to prevent further corrosion. The pre-defined profile may be a bowl shaped recess with pre-defined dimensions and substantially smooth surfaces (e.g., surface roughness lower than a certain threshold such as 10 nm). The timing matters, because applying the metal corrosion protectant prematurely would impede the formation of target recess profiles (e.g., if corrosion inhibitor is applied at the beginning, no recess may form at all), and applying the metal corrosion protectant too late may mean that the corrosion may have already occurred. In some embodiments, operation 208 soaks or immerses the device 100 shown in FIG. 5 into a new chemical containing a metal corrosion inhibitor. In other embodiments, operation 208 adds the metal corrosion inhibitor into the wet etchant used in operation 206. Various mechanisms may be used to help the metal corrosion inhibitor reach the top surfaces of the lower plugs 124a-124c, where the metal corrosion inhibitor protects underlying metals from continued etching or corrosion by the wet etchant used in operation 206. Operation 208 may last for any suitable time period and be performed at any suitable temperature. In some embodiments, operation 208 lasts between 30 to 90 seconds (e.g., about 30, about 60, or about 90 seconds).

At operation 210, the method 200 removes chemicals from operations 206 and 208, e.g., by using rinsing and drying processes. Due to the presence of the metal corrosion protectant, corrosion of the lower plugs 124a-124c is effectively reduced or prevented during the rinsing and drying processes. Therefore, profiles of the recesses 125a-125d are maintained. In some embodiments, a rinsing process uses isopropyl alcohol (IPA), acetone, methanol, other suitable rinse solutions, or combinations thereof. In some embodiments, a drying process includes spinning the device 100 on a wafer chuck to drain away any remaining chemicals. Drying may be performed at room temperature, but elevated temperature may reduce drying time.

Since chemicals and process conditions (e.g., time and temperature) used in the one operation affect the next operation, the control of operations 206, 208, and 210 may be coordinated to optimize recess profiles. In some embodiments, operations 206 and 208 are performed with a combined duration between 30 to 300 seconds and between the room temperature to about 67 degrees Celsius. An elevated temperature may help reduce process time but may impact other aspects such as functionality of wet etchant and/or metal corrosion inhibitor. The material makeup of the lower plugs 124a-124c affects the choice of wet etchant and metal corrosion inhibitor. Therefore, chemicals and process conditions may be adjusted or fine-tuned in order to optimize the formation and maintenance of tunable recess profiles.

In addition to forming tunable recess profiles, the wet cleaning process disclosed herein increases design flexibility in the sidewall profiles of via holes 127a-127d (and ultimately the sidewall profiles of upper plugs 138a-138d). For

example, in some embodiments, the etching processes in operation **204** are controlled to produce a trapezoidal sidewall profile for the via holes **127a-127d**. That is, as shown in FIG. **4** as an example, each via hole has respective a bottom opening width (W1, measured at the bottom level of the MCESL **128** as if no recess existed) that is less than a respective top opening width (W2) of the via hole. On one hand, if the via holes **127a-127d** are too slanted (e.g., W1 is less than 50% of W2), the contact area between the upper plugs and lower plugs may be too small, which leads to undesirably high resistance. On the other hand, if the via holes **127a-127d** are too upright (e.g., W1 is greater than 90% of W2), the lower corners of the via holes **127a-127d** may not be properly filled, leaving voids therein. The presence of tunable recesses at the bottom of the via holes **127a-127d** allows the ratio of W1 and W2 to be more flexible. On the one hand, even if W1 is less than 50% of W2, an upper plug and a lower plug may still have relatively low contact resistance due to the presence of the increased interfacial area. On the other hand, even if W1 is greater than 90% of W2, bowl shaped recesses at the bottom of the via hole **127a-127d** help proper filling of their lower corners. In an embodiment, W1 is between 45% to 95% (e.g., between 45% and 50%, between 50% to 90%, or between 90 and 95%) of W2.

At operation **212**, the method **200** forms the upper plugs **138a-138d**, thereby leading to the device **100** shown in FIG. **1**. The upper plugs **138a** and **138b** are grown over respective lower plugs **124a-124c** and completely fill respective via holes **127a-127d**. Due to the recesses **125a-125d**, the bottom portions of the upper plugs **138a-138d** extend into recessed top portions of the lower plugs **124a-124c**. Such a curved interface between the upper and lower plugs reduces contact resistance. The upper plugs **138a-138d** may include aluminum (Al), cobalt (Co), and/or other suitable materials. In some embodiments, the upper and lower plugs use different metal materials. Operation **212** may include a deposition process and a chemical mechanical planarization (CMP) process. Material(s) for the upper plugs **138a-138d** is first deposited in the via holes **127a-127d** and over the ILD layer **130**, and then excessive material(s) is removed via CMP from the top surface of the ILD layer **130**.

At operation **214**, the method **200** performs further processes to the device **100**. For example, the operation **214** may deposit another etch stop layer (ESL) and another ILD layer over the ILD layer **130**, etch the newly deposited ESL and ILD layers to form trenches, and deposit a metal (e.g., copper) in the trenches to form metal wires. The metal wires are configured to interconnect upper plugs including **138a-138d** as well as other circuit features. The operation **224** may repeat such process to build any number of layers of metal wires.

Although not intended to be limiting, one or more embodiments of the present disclosure provide many benefits to a semiconductor device and the formation thereof. For example, the wet cleaning process disclosed herein realizes in-situ metal recess and corrosion suppression, thereby creating determinative metal recesses without extra metal corrosion. Such metal recesses reduce contact resistance between upper and lower metal plugs and increases their design flexibility, which meets the demands for continued device down-scaling. Embodiments of the disclosed methods can be readily integrated into existing manufacturing processes and technologies, such as middle end of line (MEoL) and back end of line (BEoL) processes.

In one exemplary aspect, the present disclosure provides a method comprising providing a semiconductor structure

having a substrate, one or more first dielectric layers over the substrate, a first metal plug in the one or more first dielectric layers, and one or more second dielectric layers over the one or more first dielectric layers and the first metal plug. The method further comprises etching a via hole into the one or more second dielectric layers to expose the first metal plug, etching a top surface of the first metal plug to create a recess thereon, and applying a metal corrosion protectant comprising a metal corrosion inhibitor to the top surface of the first metal plug. In an embodiment, dimensions of the recess are controlled by adjustment of process conditions including time and temperature for the etching of the top surface of the first metal plug. In an embodiment, the metal corrosion protectant is applied to the top surface of the first metal plug after the recess has reached a pre-defined target profile. In an embodiment, the pre-defined target profile is a bowl shape with a substantially smooth surface. In an embodiment, the method further comprises removing the metal corrosion protectant and a wet etchant used in the etching of the top surface of the first metal plug, and filling a second metal plug into the via hole including the recess. In an embodiment, the etching of the top surface of the first metal plug uses an isotropic etching process. In an embodiment, the wet etchant comprises one of carbon dioxide (CO<sub>2</sub>) blended deionized (DI) water, ozone (O<sub>3</sub>) blended DI water, and hydrogen peroxide (H<sub>2</sub>O<sub>2</sub>) blended DI water. Removing the metal corrosion protectant and the wet etchant comprises performing a rinsing process that uses isopropyl alcohol (IPA), acetone, methanol, or combinations thereof. In an embodiment, the via hole is a first via hole. The method further comprises etching, simultaneously with the etching of the first via hole, a second via hole into the one or more second dielectric layers to expose the first metal plug. In an embodiment, the via hole has a bottom opening width and a top opening width, and the bottom opening width is between 90% and 95% of the top opening width. In an embodiment, the first metal plug is disposed over and electrically connected to a transistor source/drain feature or a transistor gate feature.

In another exemplary aspect, the present disclosure provides a method comprising providing a semiconductor device having a substrate, an active region over the substrate, a lower plug disposed over the active region, and at least one ILD layer over the lower plug. The method further comprises etching a via hole into the at least one ILD layer to at least partially expose a top surface of the lower plug, and performing a wet cleaning process to deepen the via hole by creating a recess on the lower plug. Dimensions of the recess are tunable by controlling process conditions of the wet cleaning process. In an embodiment, the method further comprises filling an upper plug into the via hole, wherein the lower plug and the upper plug comprise different materials. In an embodiment, the wet cleaning process comprises applying a wet etchant on the top surface of the lower plug to create the recess thereon, applying a metal corrosion inhibitor to the top surface of the lower plug, and removing the metal corrosion inhibitor and the wet etchant using rinsing and drying processes. In an embodiment, the wet etchant comprises one of carbon dioxide (CO<sub>2</sub>) blended deionized (DI) water, ozone (O<sub>3</sub>) blended DI water, and hydrogen peroxide (H<sub>2</sub>O<sub>2</sub>) blended DI water. In an embodiment, the metal corrosion inhibitor is applied to the top surface of the first metal plug only after the dimensions of the recess have reached pre-defined values. In an embodiment, the lower plug is a first lower plug, the via hole is a first via hole, and the recess is a first recess. The method further comprises etching a second via hole into the at least

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one ILD layer to at least partially expose a top surface of a second lower plug. The wet cleaning process creates a second recess on the second lower plug, and dimensions of the second recess are substantially equal to corresponding dimensions of the first lower plug.

In another exemplary aspect, the present disclosure provides a semiconductor device comprising one or more first dielectric layers disposed over a substrate, a first via disposed in the one or more first dielectric layers, one or more second dielectric layers disposed over the first via, and a second via disposed in the one or more second dielectric layers, over the first via, and electrically connected to the first via. An interface between the first and second vias comprises a bowl shaped area. In an embodiment, the semiconductor device further comprises a third via disposed in the one or more second dielectric layers, over the first via, and electrically connected to the first via. The second and third vias have about equal depth. In an embodiment, the semiconductor device further comprises a fourth via disposed in the one or more first dielectric layers, and a fifth via disposed in the one or more second dielectric layers, over the fourth via, and electrically connected to the fourth via. The second, third, and fifth vias have about equal depth. In an embodiment, the first and second vias comprise different metals.

The foregoing outlines features of several embodiments so that those of ordinary skill in the art may better understand the aspects of the present disclosure. Those of ordinary skill in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those of ordinary skill in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

What is claimed is:

1. A method comprising:

forming a first interlayer dielectric (ILD) layer over a substrate;

forming a contact etch stop layer over the first ILD layer; forming a second ILD layer over the contact etch stop layer;

forming a first metal plug that extends through the first ILD layer; and

forming a second metal plug that extends through the second ILD layer, through the contact etch stop layer, and into the first metal plug, wherein a portion of the second metal plug that extends into the first metal plug has a curved bottom that extends between a first sidewall and a second sidewall, and wherein the first metal plug wraps and abuts the curved bottom, the first sidewall, and the second sidewall, wherein the forming the second metal plug includes:

forming an interconnect opening that extends through the second ILD layer and the contact etch stop layer to expose a portion of the first metal plug,

performing a wet cleaning process that etches the exposed portion of the first metal plug to form a recess in the exposed portion of the first metal plug, thereby extending the interconnect opening into the first metal plug, wherein parameters of the wet cleaning process are tuned to provide the recess with a target profile and the wet cleaning process further includes applying a metal corrosion protectant to the

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exposed portion of the first metal plug after etching the exposed portion of the first metal plug to form the recess, wherein the metal corrosion protectant is applied upon the recess reaching the target profile, and

depositing conductive materials in the interconnect opening after performing the wet cleaning process.

2. The method of claim 1, wherein:

the etching the exposed portion of the first metal plug to form the recess in the exposed portion of the first metal plug includes soaking the exposed portion of the first metal plug in a wet etch solution; and

the applying the metal corrosion protectant to the exposed portion of the first metal plug after etching the exposed portion of the first metal plug to form the recess includes adding the metal corrosion protectant to the wet etch solution upon the recess reaching the target profile.

3. The method of claim 1, wherein the wet cleaning process further includes:

performing a rinsing process after applying the metal corrosion protectant; and

performing a drying process after applying the metal corrosion protectant.

4. The method of claim 1, wherein the etching of the exposed portion of the first metal plug to form the recess is performed for about 30 seconds to about 300 seconds.

5. The method of claim 1, wherein the etching the exposed portion of the first metal plug includes applying a solution to the exposed portion of the first metal plug, wherein the solution includes deionized water alone or blended with  $H_2O_2$ ,  $CO_2$ ,  $O_3$ , or combinations thereof.

6. The method of claim 5, wherein the solution includes deionized water blended with  $H_2O_2$  and the solution has a  $H_2O_2:H_2O$  volume ratio of about 1:5 to about 1:30.

7. The method of claim 1, wherein:

the forming the first metal plug includes forming a source/drain contact; and

the forming the second metal plug includes forming a source/drain via.

8. The method of claim 1, wherein:

the forming the first metal plug includes forming a gate contact; and

the forming the second metal plug includes forming a gate via.

9. The method of claim 1, wherein:

the forming the first metal plug includes forming a tungsten plug; and

the forming the second metal plug includes forming a cobalt plug.

10. A method comprising:

forming a gate stack over a substrate, wherein the gate stack is disposed between a first source/drain feature and a second source/drain feature disposed in the substrate;

forming a dielectric layer over the gate stack, the first source/drain feature, the second source/drain feature, and the substrate;

forming a source/drain contact in the dielectric layer, wherein the source/drain contact is disposed on the first source/drain feature;

forming a first source/drain via in the dielectric layer, wherein the first source/drain via extends into and abuts the source/drain contact, such that a bottom surface of the first source/drain via is lower than a top surface of the source/drain contact and a portion of the source/

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drain contact extends between and abuts the dielectric layer and sidewalls of the first source/drain via; and forming a second source/drain via in the dielectric layer, wherein the second source/drain via extends into and abuts the source/drain contact, such that a bottom surface of the second source/drain via is lower than a top surface of the source/drain contact and a portion of the source/drain contact extends between and abuts the dielectric layer and sidewalls of the second source/drain via.

11. The method of claim 10, further comprising:  
forming a second source/drain contact in the dielectric layer, wherein the second source/drain contact is disposed on the second source/drain feature; and  
forming a third source/drain via in the dielectric layer, wherein the third-second source/drain via extends into and abuts the second source/drain contact, such that a bottom surface of the third source/drain via is lower than a top surface of the second source/drain contact and a portion of the second source/drain contact extends between and abuts the dielectric layer and sidewalls of the third source/drain via.

12. The method of claim 10, wherein first dimensions of the first source/drain via are the same as second dimensions of the second source/drain via.

13. The method of claim 10, wherein an interface between the source/drain contact and the first source/drain via is curved.

14. The method of claim 10, wherein the source/drain contact includes a first metal fill layer, the first source/drain via includes a second metal fill layer, the first metal fill layer includes a first metal, the second metal fill layer includes a second metal, and the first metal is different than the second metal.

15. The method of claim 10, wherein the forming the first source/drain via includes:

forming a via opening in the dielectric layer that exposes the source/drain contact;  
etching the exposed source/drain contact to form a recess in the exposed source/drain contact, thereby extending the via opening into the source/drain contact, wherein the recess is formed by a first sidewall portion of the source/drain contact, a second sidewall portion of the source/drain contact, and a curved portion of the source/drain contact that extends between the first sidewall portion and the second sidewall portion;

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applying a metal corrosion protectant to the exposed source/drain contact after etching the exposed source/drain contact to form the recess; and  
filling the via opening with a conductive material.

16. The method of claim 15, wherein before filling the via opening with the conductive material, the forming the first source/drain via further includes:

performing a rinsing process; and  
performing a drying process.

17. A method comprising:  
forming a first dielectric layer over a substrate;  
forming a second dielectric layer over the first dielectric layer;

forming a first metal plug in the first dielectric layer; and  
forming a second metal plug in the second dielectric layer, wherein the second metal plug extends into the first metal plug, such that the first metal plug abuts at least three surfaces of the second metal plug, wherein the forming the second metal plug includes:

performing a first etch to form an opening in the second dielectric layer, wherein the opening exposes the first metal plug,

performing a second etch to form a recess in the exposed first metal plug, thereby extending the opening into the first metal plug, wherein the recess is formed by a first sidewall portion of the first metal plug, a second sidewall portion of the second metal plug, and a curved portion of the first metal plug, wherein the curved portion of the first metal plug extends between the first sidewall portion and the second sidewall portion, and

after performing the second etch, immersing the exposed first metal plug in a chemical containing a metal corrosion protectant, such that a metal corrosion protectant is applied to the recess in the exposed first metal plug.

18. The method of claim 17, wherein the performing the second etch includes soaking the exposed first metal plug in a deionized water solution.

19. The method of claim 17, wherein the performing the second etch includes soaking the exposed first metal plug in an ozone blended deionized water solution.

20. The method of claim 17, wherein the performing the second etch includes soaking the exposed first metal plug in a carbon dioxide blended deionized water solution.

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